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## WE CLAIM AS OUR INVENTION

- 1 14) A silicon cuvette comprising:
- 2 a silicon substrate having a chamber for containing
- 3 a microsample during analysis; and
- 4 a chamber window formed of silicon nitride
- 5 positioned over the chamber.
- 1 15) The device of claim 14, wherein the silicon
- 2 nitride has a thickness of from about 0.01 of a
- 3 micrometer to about 5 micrometers.
- 1 16) Method of constructing a window in a silicon
- 2 cuvette, comprising the steps of:
- 3 providing a silicon substrate having a top surface
- 4 and a bottom surface;
- 5 etching a depression in the top surface of the
- 6 silicon substrate defining a microsample chamber;
- 7 depositing a silicon nitride film on the top surface
- 8 of the silicon substrate and in the chamber; and
- 9 etching a depression in the bottom surface of the
- 10 silicon substrate in registration with the chamber in the
- 11 top surface for exposing the silicon nitride film within
- 12 the chamber to form the chamber window.
- 1 17) The method of Claim 16, wherein the silicon
- 2 substrate is a silicon wafer.
- 1 18) The method of Claim 16, wherein the silicon
- 2 nitride film has a thickness of from about 0.01 of a
- 3 micrometer to about 5 micrometers.

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- 19) A microsampling device for obtaining a
- 2 microsample of bodily fluid from a subject, comprising:
- . a substrate having a chamber with a sampling side
- 4 and a viewing side for containing and viewing a
- 5 microsample; and
- a chamber window formed of silicon nitride covering
- 7 the chamber for closing the viewing side.
- 20) The device of Claim 19, wherein the substrate is
- 2 silicon.
- 21) The device of Claim 20, wherein the silicon
- 2 substrate has a thickness of about 500 micrometers.
- 22) The device of Claim 19, wherein the silicon
- 2 nitride window has a thickness of from about 0.01 of a
- 3 micrometer to about 5 micrometers.
- 23) The device of Claim 19, wherein the silicon
- 2 nitride forming the window is optical quality.
- 24) The device of Claim 19, further comprising an
- 2 antireflective coating over the silicon nitride window.
- 25) The device of Claim 24, wherein the
- 2 antireflective coating is magnesium fluoride.
- 26) The device of Claim 19, wherein the chamber has
- 2 a volume of less than 1 microliter.
- 27) The device of Claim 19, further comprising a
- 2 closure member over the chamber for closing the sampling
- 3 side.

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- 28) The device of Claim 27, wherein the closure 1 2 member engages the substrate around the periphery of the 3 chamber forming an interface therebetween.
- 29) The device of Claim 28, further comprising:
- a needle formed at a needle end of the device for
- 3 obtaining the sample;
- an intake bore extending from the needle end to the
- 5 chamber along the interface between the closure member
- 6 and the substrate for transporting the sample into the
- 7 chamber.
- 30) The device of Claim 29, further comprising an 1
- 2 exhaust vent extending from the chamber away from the
- 3 needle end along the interface between the closure member
- 4 and the substrate for venting the chamber as the sample
- 5 is transported into the chamber.
- 31) The device of Claim 30, wherein the bore and the
- 2 vent are formed in the substrate.
- 32) Method of constructing a chamber window in a
- 2 microsample chamber, comprising the steps of:
- providing a silicon substrate having a sampling side
- 4 and a viewing side;
- etching a depression in the sampling side of the
- 6 silicon substrate defining a microsample chamber;
- depositing a silicon nitride film on the sampling
- 8 side of the silicon substrate and in the microsample
- 9 chamber; and
- etching a depression in the viewing side of the 10
- 11 silicon substrate in registration with the microsample
- 12 chamber in the sampling side for exposing the silicon
- 13 nitride film within the microsample chamber to form the
- 14 chamber window.

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Preliminary Amendment

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- 1 33) The method of Claim 32, wherein the silicon substrate has a thickness of about 500 micrometers.
- 1 34) The method of Claim 32, wherein the silicon
- 2 nitride film has a thickness of from about 0.01 of a
- 3 micrometer to about 5 micrometers.